



# Модуль диодный МДД-1000-18



Средний прямой ток				I <sub>FAV</sub>		1000 А				
Повторяющееся импульсное обратное напряжение				U <sub>RRM</sub>		600 - 1800 В				
U <sub>RRM</sub> , В	600	700	800	900	1000	1200	1400	1600	1800	
Класс по напряжению	6	7	8	9	10	12	14	16	18	
T <sub>j</sub> , °C	– 60 ÷ 150									

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T <sub>j</sub> (°C)	VALUE			UNIT
				Min	Type	Max	
I <sub>F(AV)</sub>	Mean forward current	180° half sine wave 50Hz Single side cooled, T <sub>C</sub> =100°C	150			1000	A
I <sub>F</sub> (RMS)	RMS forward current		150			1570	A
V <sub>RRM</sub>	Repetitive peak reverse voltage	V <sub>RRM</sub> tp=10ms V <sub>RSM</sub> = V <sub>RRM</sub> +100V	150	600		1800	V
I <sub>RRM</sub>	Repetitive peak current	at V <sub>RRM</sub>	150			50	mA
I <sub>FSM</sub>	Surge forward current	10ms half sine wave	150			28	KA
I <sup>2</sup> t	I <sup>2</sup> T for fusing coordination	V <sub>R</sub> =0.6V <sub>RRM</sub>				3920	A <sup>2</sup> s*10 <sup>3</sup>
V <sub>FO</sub>	Threshold voltage		150			0.71	V
r <sub>F</sub>	Forward slop resistance					0.10	mΩ
V <sub>FM</sub>	Peak forward voltage	I <sub>FM</sub> =3000A	25			1.82	V
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	At 180° sine Single side cooled				0.052	°C /W
R <sub>th(c-h)</sub>	Thermal resistance case to heatsink	At 180° sine Single side cooled				0.020	°C /W
V <sub>iso</sub>	Isolation voltage	50Hz,R.M.S,t=1min, I <sub>iso</sub> :1mA(max)	2500				V
F <sub>m</sub>	Terminal connection torque(M12)				14		N·m
	Mounting torque(M8)				12		N·m
T <sub>stg</sub>	Stored temperature			-40		125	°C
W <sub>t</sub>	Weight				3800		g
Outline	MDT7A						

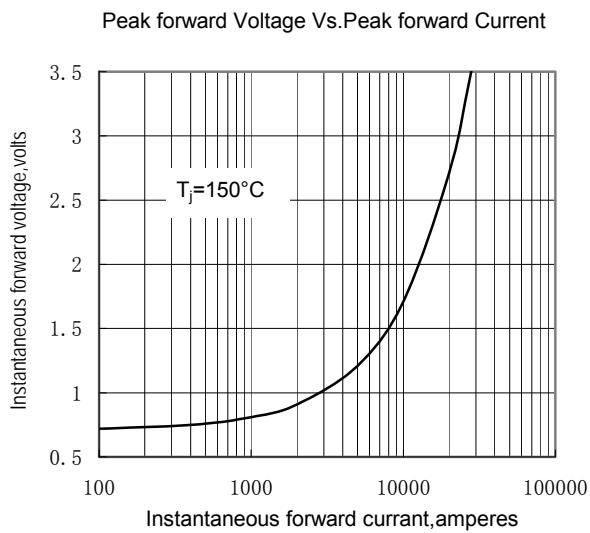


Fig.1

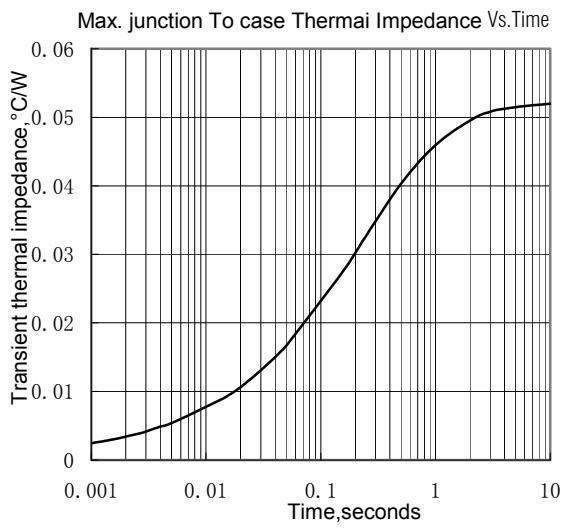


Fig.2

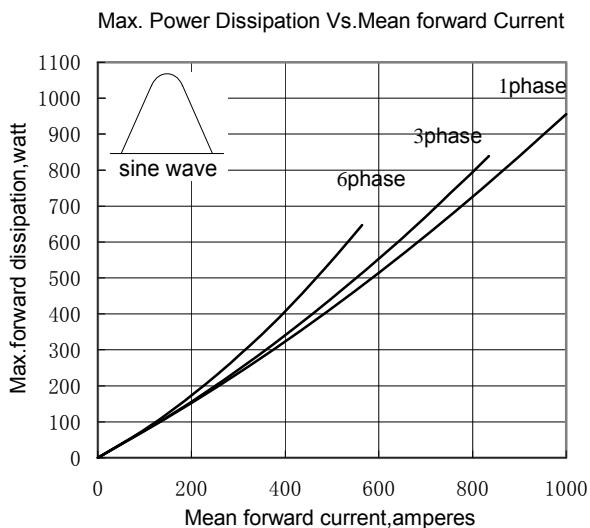


Fig.3

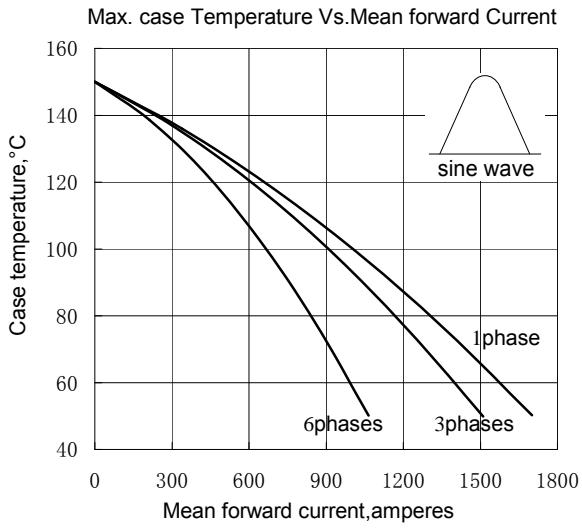


Fig.4

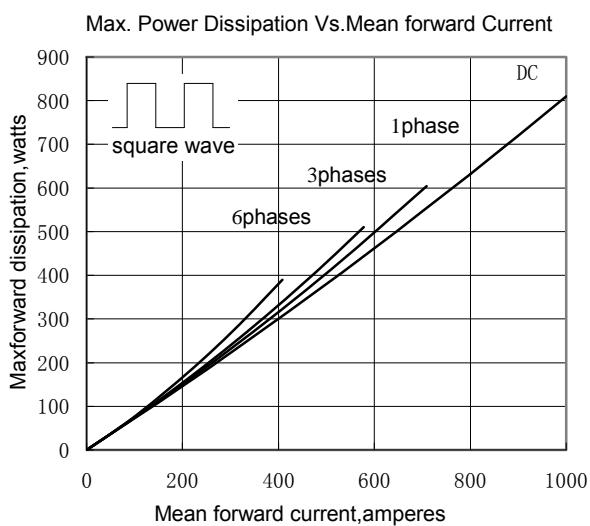


Fig.5

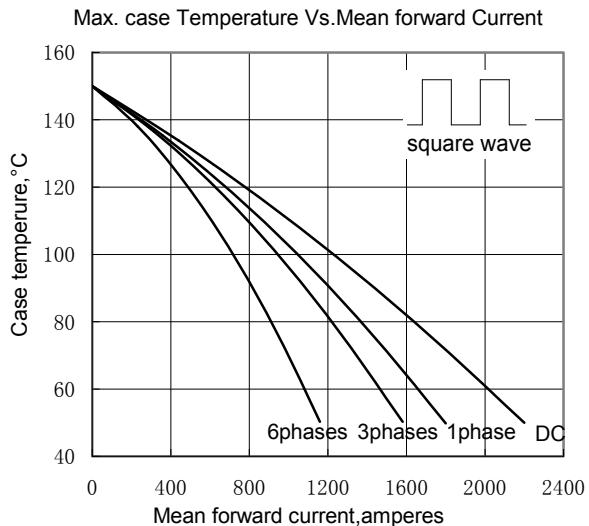


Fig.6

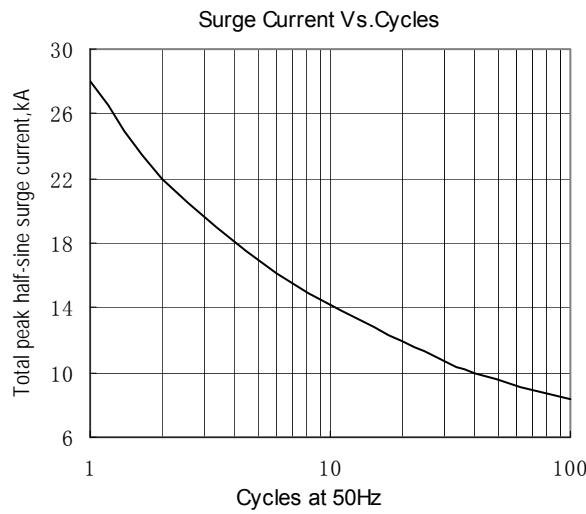


Fig.7

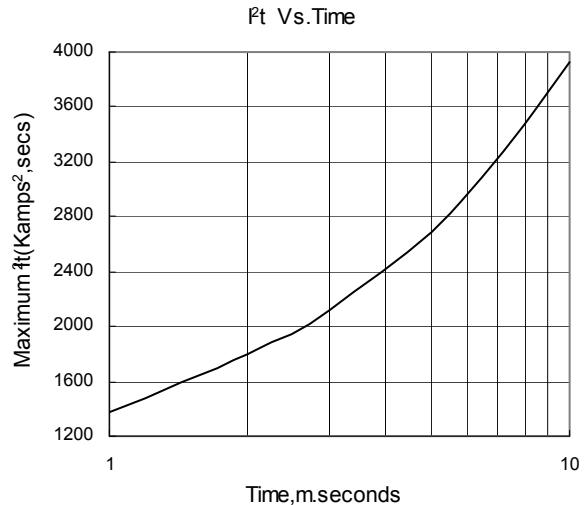
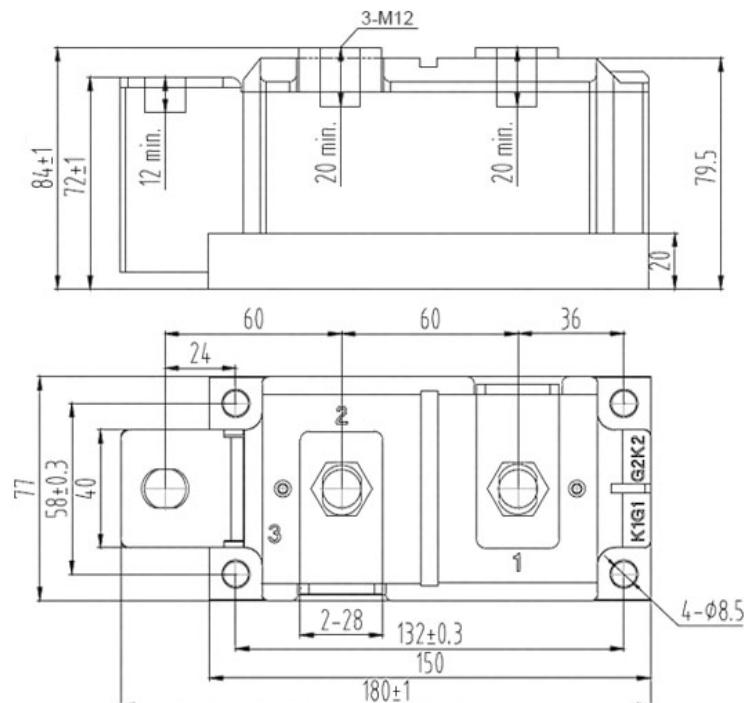


Fig.8

### ГАБАРИТНЫЕ РАЗМЕРЫ

Тип корпуса: MDT7A



Все размеры в миллиметрах



3 – Анод/Катод, 2 – Катод, 1 – Анод